# INTEGRATED CIRCUITS



Product specification Replaces data of 1997 May 12 IC23 Data Handbook

1998 Feb 13



Philips Semiconductors

### 74ALVT16600

#### **FEATURES**

- 18-bit bidirectional bus interface
- 5V I/O Compatible
- 3-State buffers
- Output capability: +64mA/-32mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5V supply
- Bus-hold data inputs eliminate the need for external pull-up resistors to hold unused inputs
- Live insertion/extraction permitted
- Power-up reset
- Power-up 3-State
- No bus current loading when output is tied to 5V bus
- Negative edge-triggered clock inputs
- Latch-up protection exceeds 500mA per JEDEC JC40.2 Std 17
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model

#### DESCRIPTION

The 74ALVT16600 is a high-performance BiCMOS product designed for  $V_{CC}$  operation at 2.5V and 3.3V with I/O compatibility up to 5V.

This device is an 18-bit universal transceiver featuring non-inverting 3-State bus compatible outputs in both send and receive directions. Data flow in each direction is controlled by output enable (OEAB and OEBA), latch enable (LEAB and LEBA), and clock (CPAB and CPBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is High. When LEAB is Low, the A data is latched if CPAB is held at a High or Low logic level. If LEAB is Low, the A-bus data is stored in the latch/flip-flop on the High-to-Low transition of CPAB. When OEAB is Low, the outputs are active. When OEAB is High, the outputs are in the high-impedance state. The High clock can be controlled with the clock-enable inputs (CEBA/CEAB).

Data flow for B-to-A is similar to that of A-to-B but uses  $\overline{\text{OEBA}}$ , LEBA and  $\overline{\text{CPBA}}$ .

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

### QUICK REFERENCE DATA

SYMBOL	DADAMETED	CONDITIONS	TYPI	LINUT	
SYMBOL	PARAMETER	T <sub>amb</sub> = 25℃	2.5V	3.3V	UNIT
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay An to Bn or Bn to An	$C_L = 50 pF$	1.9 2.5	1.6 1.9	ns
C <sub>IN</sub>	Input capacitance DIR, OE	$V_I = 0V \text{ or } V_{CC}$	4	4	pF
C <sub>I/O</sub>	I/O pin capacitance	Outputs disabled; $V_{I/O} = 0V$ or $V_{CC}$	8	8	pF
I <sub>CCZ</sub>	Total supply current	Outputs disabled	40	70	μΑ

#### **ORDERING INFORMATION**

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
56-Pin Plastic SSOP Type III	–40°C to +85°C	74ALVT16600 DL	AV16600 DL	SOT371-1
56-Pin Plastic TSSOP Type II	–40°C to +85°C	74ALVT16600 DGG	AV16600 DGG	SOT364-1

### **PIN DESCRIPTION**

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1, 27	OEAB/OEBA	A-to-B Output enable input (active Low)
29, 56	CEBA/CEAB	B-to-A / A-to-B clock enable (active Low)
2, 28	LEAB/LEBA	A-to-B/B-to-A Latch enable input
55,30	CPAB/CPBA	A-to-B/B-to-A Clock input (active falling edge)
3, 5, 6, 8, 9, 10, 12, 13, 14, 15, 16, 17, 19, 20, 21, 23, 24, 26	A0-A17	Data inputs/outputs (A side)
54, 52, 51, 49, 48, 47, 45, 44, 43, 42, 41, 40, 38, 37, 36, 34, 33, 31	B0-B17	Data inputs/outputs (B side)
4, 11, 18, 25, 32, 39, 46, 53	GND	Ground (0V)
7, 22, 35, 50	V <sub>CC</sub>	Positive supply voltage

## 74ALVT16600

### **FUNCTION TABLE**

	INPUTS							
CEAB	OEAB	LEAB	CPAB	Α	В			
Х	Н	Х	Х	Х	Z			
Х	L	Н	Х	L	L			
Х	L	Н	Х	Н	Н			
Н	L	L	Х	Х	Β <sub>Ο</sub> ±			
L	L	L	$\downarrow$	L	L			
L	L	L	$\downarrow$	Н	Н			
L	L	L	Н	Х	Β <sub>Ο</sub> ±			
L	L	L	L	Х	В <sub>О</sub> §			

X =Don't care

H =High voltage level

L = Low voltage level

 $\downarrow$  =High-to-Low clock transition

 A-to-B data flow is shown: B-to-A flow is similar but uses OEBA, LEBA, CPBA, and CEBA.

 $\pm$  Output level before the indicated steady-state input conditions were established.

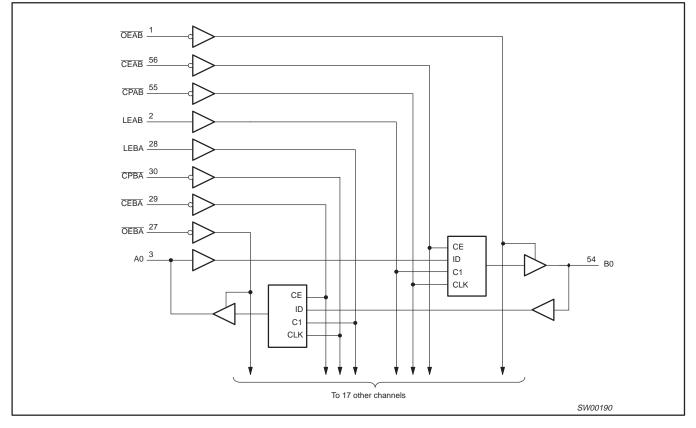
§ Output level before the indicated steady-state input conditions were established, provided that CLKAB was Low before LEAB went Low.

#### **PIN CONFIGURATION**

	_			
OEAB	1	-	56	CEAB
LEAB	2		55	CPAB
A0	3		54	В0
GND	4		53	GND
A1	5		52	B1
A2	6		51	B2
VCC	7		50	VCC
A3	8		49	В3
A4	9		48	B4
A5	10		47	B5
GND	11		46	GND
A6	12		45	B6
A7	13		44	B7
A8	14		43	B8
A9	15		42	В9
A10	16		41	B10
A11	17		40	B11
GND	18		39	GND
A12	19		38	B12
A13	20		37	B13
A14	21		36	B14
VCC	22		35	VCC
A15	23		34	B15
A16	24		33	B16
GND	25		32	GND
A17	26		31	B17
OEBA	27		30	CPBA
LEBA	28		29	CEBA
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### LOGIC DIAGRAM (Positive Logic)



### ABSOLUTE MAXIMUM RATINGS<sup>1, 2</sup>

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V <sub>CC</sub>	DC supply voltage		-0.5 to +4.6	V
I <sub>IK</sub>	DC input diode current	V <sub>1</sub> < 0	-50	mA
VI	DC input voltage <sup>3</sup>		-0.5 to +7.0	V
I <sub>OK</sub>	DC output diode current	V <sub>O</sub> < 0	-50	mA
V <sub>OUT</sub>	DC output voltage <sup>3</sup>	Output in Off or High state	-0.5 to +7.0	V
		Output in Low state	128	
IOUT	DC output current	Output in High state	-64	mA
T <sub>stg</sub>	Storage temperature range		-65 to +150	°C

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

3. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

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Product specification

### **RECOMMENDED OPERATING CONDITIONS**

SYMBOL	PARAMETER	2.5V RAN	GE LIMITS	3.3V RAN	GE LIMITS	UNIT
STWDUL		MIN	MAX	MIN	MAX	UNIT
V <sub>CC</sub>	DC supply voltage	2.3	2.7	3.0	3.6	V
VI	Input voltage	0	5.5	0	5.5	V
VIH	High-level input voltage	1.7		2.0		V
V <sub>IL</sub>	Input voltage		0.7		0.8	V
I <sub>OH</sub>	High-level output current		-8		-32	mA
le:	Low-level output current		8		32	mA
IOL	Low-level output current; current duty cycle $\leq$ 50%; f $\geq$ 1kHz		24		64	IIIA
$\Delta t / \Delta v$	Input transition rise or fall rate; Outputs enabled		10		10	ns/V
T <sub>amb</sub>	Operating free-air temperature range	-40	+85	-40	+85	°C

#### DC ELECTRICAL CHARACTERISTICS (3.3V ± 0.3V RANGE)

					LIMITS		
SYMBOL	PARAMETER	TEST CONDITIONS		Temp =	-40°C to	+85°C	UNIT
				MIN	TYP <sup>1</sup>	MAX	
V <sub>IK</sub>	Input clamp voltage	$V_{CC} = 3.0V; I_{IK} = -18mA$			-0.85	-1.2	V
\/	High-level output voltage	$V_{CC} = 3.0 \text{ to } 3.6 \text{V}; \text{ I}_{OH} = -100 \mu \text{A}$		V <sub>CC</sub> -0.2	V <sub>CC</sub>		v
V <sub>OH</sub>	High-level output voltage	V <sub>CC</sub> = 3.0V; I <sub>OH</sub> = -32mA	$V_{CC} = 3.0V; I_{OH} = -32mA$		2.3		v
		$V_{CC} = 3.0V; I_{OL} = 100\mu A$			0.07	0.2	
V <sub>OL</sub>	Low-level output voltage	V <sub>CC</sub> = 3.0V; I <sub>OL</sub> = 16mA			0.25	0.4	V
		V <sub>CC</sub> = 3.0V; I <sub>OL</sub> = 32mA			0.3	0.5	
		V <sub>CC</sub> = 3.0V; I <sub>OL</sub> = 64mA			0.4	0.55	
V <sub>RST</sub>	Power-up output low voltage <sup>6</sup>	$V_{CC}$ = 3.6V; $I_{O}$ = 1mA; $V_{I}$ = $V_{CC}$ or GND				0.55	V
		$V_{CC} = 3.6V; V_I = V_{CC} \text{ or } GND$	Control pins		0.1	±1	
		$V_{CC} = 0 \text{ or } 3.6 \text{V}; \text{ V}_{\text{I}} = 5.5 \text{V}$			0.1	10	
I <sub>I</sub>	II Input leakage current	$V_{CC} = 3.6V; V_{I} = 5.5V$		1	0.1	20	μA
		$V_{CC} = 3.6V; V_{I} = V_{CC}$	Data pins <sup>4</sup>		0.5	10	
		$V_{CC} = 3.6V; V_{I} = 0V$	1		0.1	-5	
I <sub>OFF</sub>	Off current	$V_{CC} = 0V; V_{I} \text{ or } V_{O} = 0 \text{ to } 4.5V$	•		0.1	±100	μA
	Bus Hold current	$V_{CC} = 3V; V_I = 0.8V$		75	130		
I <sub>HOLD</sub>	Data inputs <sup>7</sup>	$V_{CC} = 3V; V_{I} = 2.0V$		-75	-140		μA
	Data Inputs	$V_{CC} = 0V$ to 3.6V; $V_{CC} = 3.6V$		±500			
$I_{\text{EX}}$	Current into an output in the High state when $V_O > V_{CC}$	V <sub>O</sub> = 5.5V; V <sub>CC</sub> = 3.0V			10	125	μΑ
I <sub>PU/PD</sub>	Power up/down 3-State output current <sup>3</sup>	$V_{CC} \le 1.2$ V; $V_{O} = 0.5$ V to $V_{CC}$ ; $V_{I} = GNE$ $\overline{OE} = Don't$ care	$V_{CC} \le 1.2$ V; $V_0 = 0.5$ V to $V_{CC}$ ; $V_I = GND$ or $V_{CC}$ $\overline{OE} = Don't$ care		1.0	±100	μΑ
ICCH		$V_{CC}$ = 3.6V; Outputs High, $V_I$ = GND or $V_{CC}$ , $I_O$ = 0			0.06	0.1	1
I <sub>CCL</sub>	Quiescent supply current	$V_{CC}$ = 3.6V; Outputs Low, $V_{I}$ = GND or V	/ <sub>CC,</sub> I <sub>O =</sub> 0		4.0	5	mA
I <sub>CCZ</sub>	1	$V_{CC}$ = 3.6V; Outputs Disabled; $V_{I}$ = GND	) or $V_{CC, I_{O}} = 0^5$		0.06	0.1	
$\Delta I_{CC}$	Additional supply current per input pin <sup>2</sup>	$V_{CC} = 3V$ to 3.6V; One input at $V_{CC}$ -0.6 Other inputs at $V_{CC}$ or GND	V,		0.04	0.4	mA

#### NOTES:

All typical values are at V<sub>CC</sub> = 3.3V and T<sub>amb</sub> = 25°C.
This is the increase in supply current for each input at the specified voltage level other than V<sub>CC</sub> or GND
This parameter is valid for any V<sub>CC</sub> between 0V and 1.2V with a transition time of up to 10msec. From V<sub>CC</sub> = 1.2V to V<sub>CC</sub> = 3.3V ± 0.3V a transition time of 100µsec is permitted. This parameter is valid for T<sub>amb</sub> = 25°C only.
Unused pins at V<sub>CC</sub> or GND.

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I<sub>CCZ</sub> is measured with outputs pulled up to V<sub>CC</sub> or pulled down to ground.
For valid test results, data must not be loaded into the flip-flops (or latches) after applying power.

7. This is the bus hold overdrive current required to force the input to the opposite logic state.

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### AC CHARACTERISTICS (3.3V ±0.3V RANGE)

GND = 0V;  $t_R = t_F = 2.5ns$ ;  $C_L = 50pF$ ;  $R_L = 500\Omega$ ;  $T_{amb} = -40^{\circ}C$  to +85°C.

SYMBOL	PARAMETER	WAVEFORM	Vc	UNIT		
			MIN	TYP <sup>1</sup>	MAX	
f <sub>MAX</sub>	Maximum clock frequency	1		300		MHz
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay An to Bn or Bn to An	2	1.0 1.0	1.6 1.9	2.3 2.8	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay Clock Low or High LEAB to Bn or LEBA to An	3	1.5 1.5	2.2 2.5	3.3 4.2	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay CPAB to Bn or CPBA to An	1	1.5 1.5	2.6 3.2	4.2 4.8	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output enable time to High and Low level	5 6	1.5 1.0	2.2 1.6	3.4 2.6	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output disable time from High and Low Level	5 6	1.5 1.5	2.6 2.3	3.8 3.5	ns

NOTE:

1. All typical values are at V<sub>CC</sub> = 3.3V and T<sub>amb</sub> = 25°C.

### AC SETUP REQUIREMENTS (3.3V ±0.3V RANGE)

GND = 0V;  $t_R = t_F = 2.5ns$ ;  $C_L = 50pF$ ,  $R_L = 500\Omega$ ;  $T_{amb} = -40^{\circ}C$  to +85°C.

			LIM		
SYMBOL	PARAMETER	WAVEFORM	V <sub>CC</sub> = 3.3	UNIT	
			MIN	TYP <sup>1</sup>	
ts(H) ts(L)	Setup time, High or Low An to CPAB or Bn to CPBA	4	2.0 2.0	0.8 0.9	ns
th(H) th(L)	Hold time, High or Low An to CPAB or Bn to CPBA	4	0.0 0.0	-0.9 -0.7	ns
ts(H) ts(L)	Setup time, High or Low Clock Low An to LEAB or Bn to CPBA	4	1.0 1.0	-0.4 -0.1	ns
th(H) th(L)	Hold time, High or Low Clock High An to LEAB or Bn to LEBA	4	1.0 1.0	0.1 0.4	ns
ts(H) ts(L)	Setup time CEAB before CPAB or CEBA before CPBA	4	1.5 1.0	0.3 0.6	ns
th(H) th(L)	Hold time CEAB after CPAB or CEBA after CPBA	4	1.5 1.0	0.7 0.2	ns
tw(H) tw(L)	Pulse width, High or Low CPAB or CPBA	1	1.5 1.5		ns
tw(H)	LEAB or LEBA pulse width, High	3	1.5		ns

NOTE:

1. All typical values are at V\_{CC} = 3.3V and T\_{amb} = 25°C.

### DC ELECTRICAL CHARACTERISTICS (2.5V $\pm$ 0.2V RANGE)

					LIMITS		
SYMBOL	PARAMETER	TEST CONDITIONS		Temp = -40°C to +85°C			UNIT
				MIN	TYP <sup>1</sup>	MAX	
V <sub>IK</sub>	Input clamp voltage	V <sub>CC</sub> = 2.3V; I <sub>IK</sub> = -18mA			-0.85	-1.2	V
	L Park Jacob and and and the sec	$V_{CC} = 2.3 \text{ to } 3.6 \text{V}; \text{ I}_{OH} = -100 \mu \text{A}$		V <sub>CC</sub> -0.2			N
V <sub>OH</sub>	High-level output voltage	V <sub>CC</sub> = 2.3V; I <sub>OH</sub> = -8mA		1.8			V
		V <sub>CC</sub> = 2.3V; I <sub>OL</sub> = 100µA			0.07	0.2	
V <sub>OL</sub>	Low-level output voltage	V <sub>CC</sub> = 2.3V; I <sub>OL</sub> = 24mA			0.3	0.5	V
		V <sub>CC</sub> = 2.3V; I <sub>OL</sub> = 8mA				0.4	1
V <sub>RST</sub>	Power-up output low voltage <sup>7</sup>	$V_{CC}$ = 2.7V; $I_{O}$ = 1mA; $V_{I}$ = $V_{CC}$ or GND				0.55	V
		$V_{CC} = 2.7V; V_I = V_{CC}$ or GND	Control pins		0.1	±1	
	II Input leakage current	V <sub>CC</sub> = 0 or 2.7V; V <sub>I</sub> = 5.5V			0.1	10	
I <sub>I</sub>		V <sub>CC</sub> = 2.7V; V <sub>I</sub> = 5.5V			0.1	20	μA
		$V_{CC} = 2.7V; V_{I} = V_{CC}$	Data pins <sup>4</sup>		0.1	1	
		$V_{CC} = 2.7V; V_{I} = 0$	1		0.1	-5	1
I <sub>OFF</sub>	Off current	$V_{CC} = 0V$ ; $V_{I}$ or $V_{O} = 0$ to 4.5V			0.1	±100	μA
I <sub>HOLD</sub>	Bus Hold current	V <sub>CC</sub> = 2.3V; V <sub>I</sub> = 0.7V			90		۵
HOLD	Data inputs <sup>6</sup>	V <sub>CC</sub> = 2.3V; V <sub>I</sub> = 1.7V			-75		μA
I <sub>EX</sub>	Current into an output in the High state when $V_O > V_{CC}$	V <sub>O</sub> = 5.5V; V <sub>CC</sub> = 2.3V			10	125	μA
I <sub>PU/PD</sub>	Power up/down 3-State output current <sup>3</sup>	$\frac{V_{CC} \le 1.2V}{OE} = 0.5V$ to $V_{CC}$ ; $V_I = GNE$	$V_{CC} \le 1.2V$ ; $V_O = 0.5V$ to $V_{CC}$ ; $V_I = GND$ or $V_{CC}$ ; $\overline{OE} = Don't$ care		1	100	μA
I <sub>CCH</sub>		$V_{CC} = 2.7V$ ; Outputs High, $V_I = GND$ or $V_{CC}$	V <sub>CC</sub> , I <sub>O =</sub> 0		0.04	0.1	
I <sub>CCL</sub>	Quiescent supply current	$V_{CC}$ = 2.7V; Outputs Low, $V_{I}$ = GND or V	$V_{CC} = 2.7V$ ; Outputs Low, $V_I = GND$ or $V_{CC}$ , $I_O = 0$		3.0	4.5	mA
I <sub>CCZ</sub>	1	$V_{CC}$ = 2.7V; Outputs Disabled; $V_{I}$ = GND	) or $V_{CC, I_{O}} = 0^5$		0.04	0.1	
$\Delta I_{CC}$	Additional supply current per input pin <sup>2</sup>	$V_{CC}$ = 2.3V to 2.7V; One input at $V_{CC}$ -0. Other inputs at $V_{CC}$ or GND	.6V,		0.01	0.4	mA

NOTES:

All typical values are at V<sub>CC</sub> = 2.5V and T<sub>amb</sub> = 25°C.
This is the increase in supply current for each input at the specified voltage level other than V<sub>CC</sub> or GND
This parameter is valid for any V<sub>CC</sub> between 0V and 1.2V with a transition time of up to 10msec. From V<sub>CC</sub> = 1.2V to V<sub>CC</sub> = 2.5V ± 0.2V a transition time of 100µsec is permitted. This parameter is valid for T<sub>amb</sub> = 25°C only.
Unused pins at V<sub>CC</sub> or GND.

5.  $I_{\mbox{CCZ}}$  is measured with outputs pulled up to  $V_{\mbox{CC}}$  or pulled down to ground.

6. Not guaranteed.

7. For valid test results, data must not be loaded into the flip-flops (or latches) after applying power.

### 74ALVT16600

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### AC CHARACTERISTICS (2.5V ±0.2V RANGE)

GND = 0V;  $t_R = t_F = 2.5ns$ ;  $C_L = 50pF$ ;  $R_L = 500\Omega$ ;  $T_{amb} = -40^{\circ}C$  to +85°C.

				UNIT		
SYMBOL	PARAMETER	WAVEFORM	Vc			
			MIN	TYP <sup>1</sup>	MAX	
f <sub>MAX</sub>	Maximum clock frequency	1		250		MHz
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay An to Bn or Bn to An	2	1.0 1.5	1.9 2.5	3.0 3.6	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay Clock Low or High LEAB to Bn or LEBA to An	3	2.0 2.5	3.0 3.3	4.5 5.1	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation delay CPAB to Bn or CPBA to An	1	2.5 2.5	3.8 4.5	5.6 6.7	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output enable time to High and Low level	5 6	2.0 1.0	3.1 2.0	4.4 3.0	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output disable time from High and Low Level	5 6	1.5 1.5	2.5 2.3	4.1 3.6	ns

NOTE:

1. All typical values are at V<sub>CC</sub> = 3.3V and  $T_{amb}$  = 25°C.

### AC SETUP REQUIREMENTS (2.5V $\pm$ 0.2V RANGE)

GND = 0V;  $t_R = t_F = 2.5ns$ ;  $C_L = 50pF$ ,  $R_L = 500\Omega$ ;  $T_{amb} = -40^{\circ}C$  to +85°C.

			LIMITS		UNIT	
SYMBOL	PARAMETER	WAVEFORM	$V_{CC}$ = 2.5V $\pm$ 0.2V			
			MIN	TYP <sup>1</sup>		
ts(H) ts(L)	Setup time, High or Low An to CPAB or Bn to CPBA	4	1.5 2.0	0.5 1.1	ns	
th(H) th(L)	Hold time, High or Low An to CPAB or Bn to CPBA	4	0.0 1.0	-1.1 -0.4	ns	
ts(H) ts(L)	Setup time, High or Low Clock Low An to LEAB or Bn to CPBA	4	0.0 1.5	-0.8 0.4	ns	
th(H) th(L)	Hold time, High or Low Clock High An to LEAB or Bn to LEBA	4	1.0 1.5	-0.4 0.9	ns	
ts(H) ts(L)	Setup time CEAB before CPAB or CEBA before CPBA	4	1.0 1.0	-0.3 -0.5	ns	
th(H) th(L)	Hold time CEAB after CPAB or CEBA after CPBA	4	1.5 1.5	0.8 0.5	ns	
tw(H) tw(L)	Pulse width, High or Low CPAB or CPBA	1	2.5 2.5		ns	
tw(H)	LEAB or LEBA pulse width, High	3	1.5		ns	

NOTE:

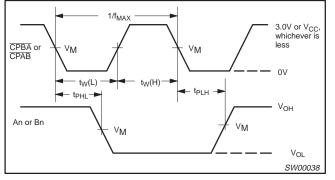
1. All typical values are at  $V_{CC}$  = 2.5V and  $T_{amb}$  = 25°C.

### 74ALVT16600

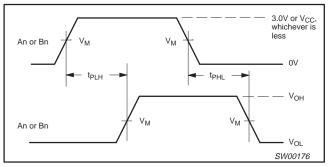
#### AC WAVEFORMS

#### NOTES:

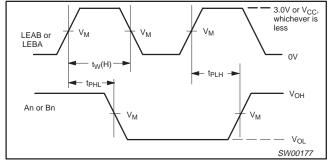
- 1.  $V_M = 1.5V$  at  $V_{CC} \ge 3.0V$ ,  $V_M = V_{CC}/2$  at  $V_{CC} \le 2.7V$ 2.  $V_X = V_{OL} + 0.3V$  at  $V_{CC} \ge 3.0V$ ,  $V_X = V_{OL} + 0.15V$  at  $V_{CC} \le 2.7V$ 3.  $V_Y = V_{OH} 0.3V$  at  $V_{CC} \ge 3.0V$ ,  $V_Y = V_{OH} 0.15V$  at  $V_{CC} \le 2.7V$



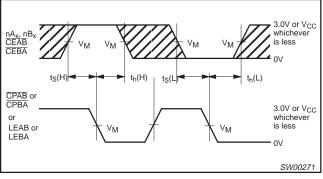
Waveform 1. Propagation Delay, Clock Input to Output, Clock Pulse Width, and Maximum Clock Frequency



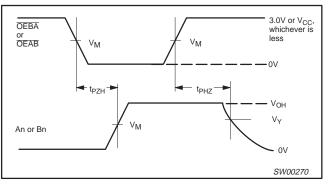
Waveform 2. Propagation Delay, Transparent Mode



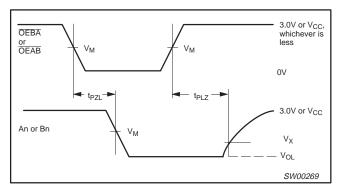
Waveform 3. Propagation Delay, Enable to Output, and Enable Pulse Width



Waveform 4. Data Setup and Hold Times



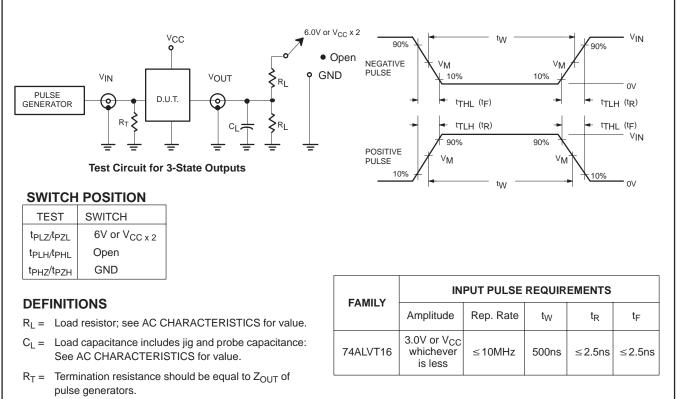
Waveform 5. 3-State Output Enable Time to High Level and Output Disable Time from High Level



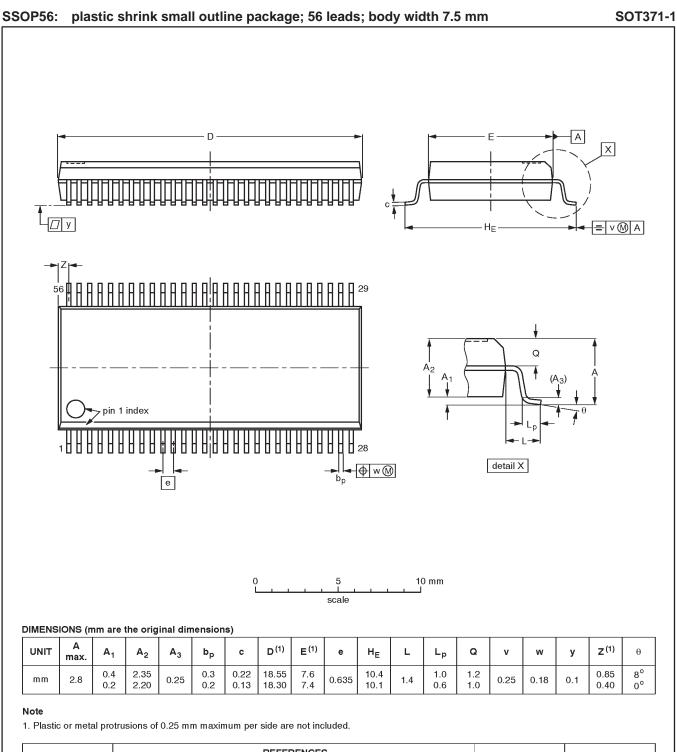
Waveform 6. 3-State Output Enable Time to Low Level and Output Disable Time from Low Level

## 74ALVT16600

### **TEST CIRCUIT AND WAVEFORMS**



### 74ALVT16600

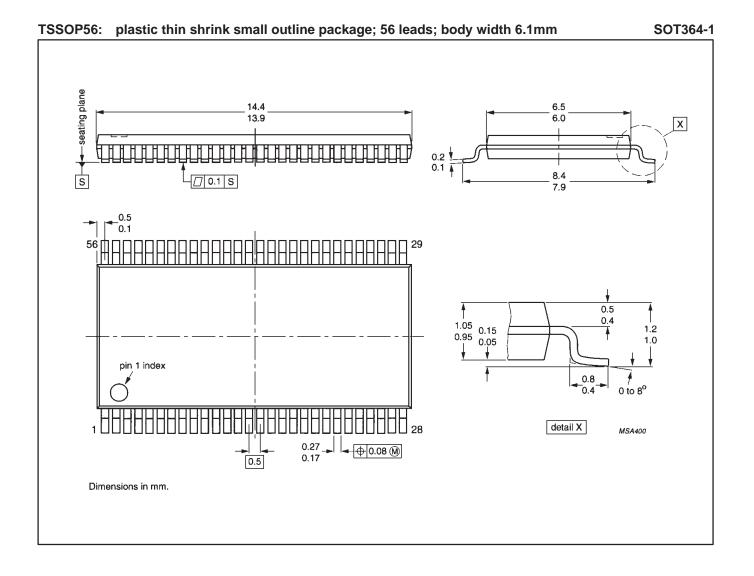


OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT371-1		MO-118AB				<del>-93-11-02</del> 95-02-04

**Philips Semiconductors** 

# 2.5V/3.3V 18-bit universal bus transceiver (3-State)

# 74ALVT16600



74ALVT16600

NOTES

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### 74ALVT16600

#### Data sheet status

Data sheet status	Product status	Definition [1]
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